

**UP0187B**

## Silicon N-channel MOSFET

For switching circuits

## ■ Features

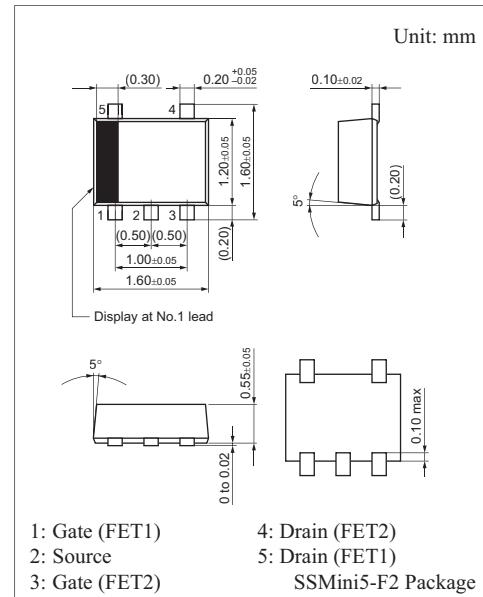
- High-speed switching
- Incorporating a built-in gate protection-diode
- Two elements incorporated into one package
- SSMini type package, reduction of the mounting area and assembly cost

### ■ Basic Part Number

- 2SK3938 × 2

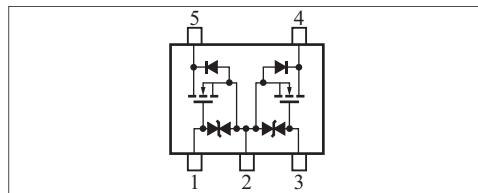
### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	$V_{DSS}$	30	V
Gate-source surrender voltage	$V_{GSS}$	$\pm 12$	V
Drain current	$I_D$	100	mA
Peak drain current	$I_{DP}$	200	mA
Total power dissipation	$P_T$	125	mW
Channel temperature	$T_{ch}$	125	°C
Storage temperature	$T_{stg}$	-55 to +125	°C



Marking Symbol: 4M

## Internal Connection

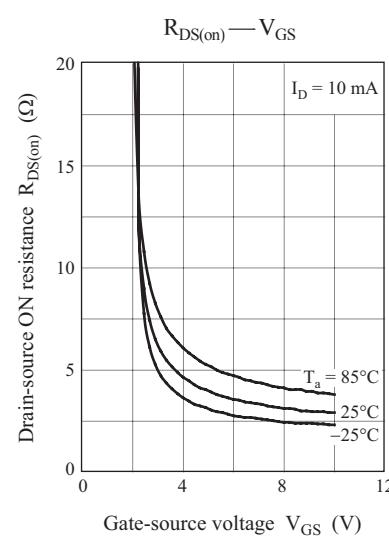
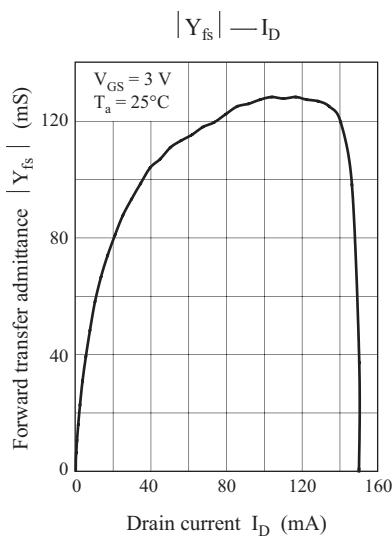
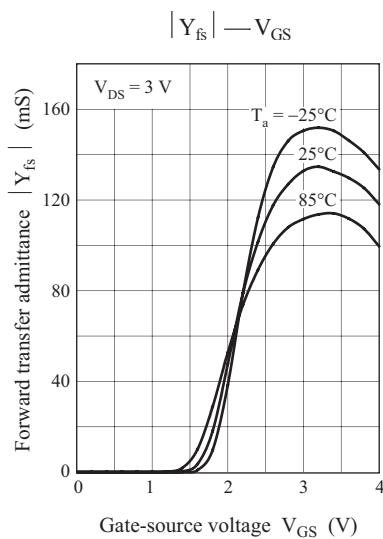
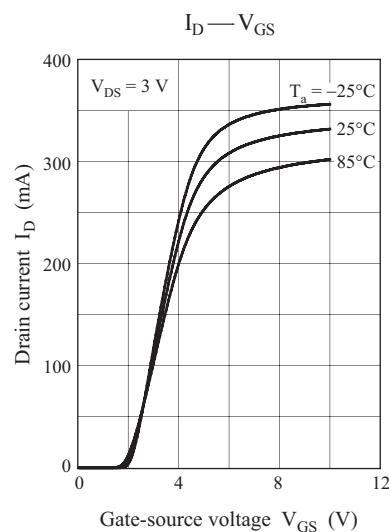
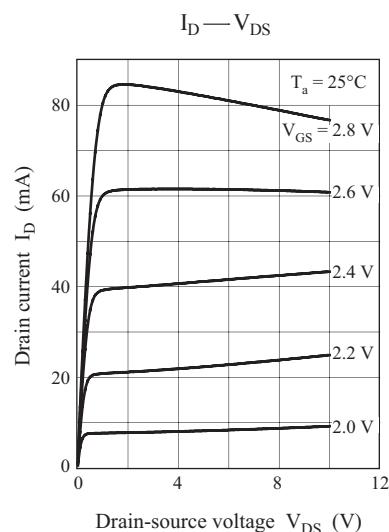
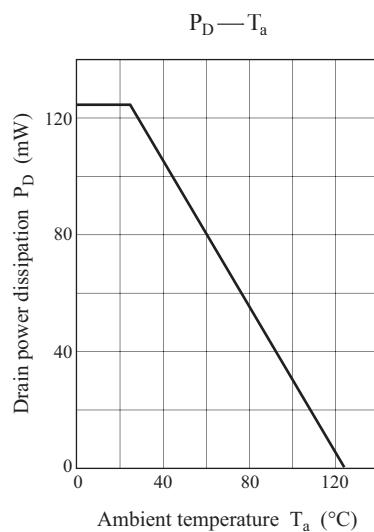
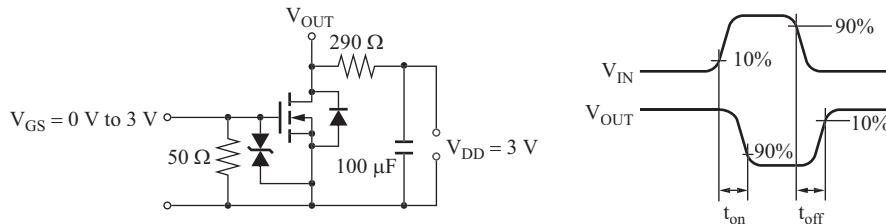


## ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	$V_{DSS}$	$I_D = 10 \mu A, V_{GS} = 0$	30			V
Drain-source cutoff current	$I_{DSS}$	$V_{DS} = 20 V, V_{GS} = 0$			1.0	$\mu A$
Gate-source cutoff current	$I_{GSS}$	$V_{GS} = \pm 10 V, V_{DS} = 0$			$\pm 10$	$\mu A$
Gate threshold voltage	$V_{TH}$	$I_D = 1.0 \mu A, V_{DS} = 3.0 V$	0.5	1.0	1.5	V
Drain-source ON resistance	$R_{DS(on)}$	$I_D = 10 mA, V_{GS} = 2.5 V$		7	12	$\Omega$
		$I_D = 10 mA, V_{GS} = 4.0 V$		5	8	
Forward transfer admittance	$ Y_{fs} $	$I_D = 10 mA, V_{DS} = 3 V, f = 1 kHz$	20	55		mS
Short-circuit input capacitance (Common source)	$C_{iss}$	$V_{DS} = 3 V, V_{GS} = 0, f = 1 MHz$		12		pF
Short-circuit output capacitance (Common source)	$C_{oss}$			10		pF
Reverse transfer capacitance (Common source)	$C_{rss}$			6		pF
Turn-on time *	$t_{on}$	$V_{DD} = 3 V, V_{GS} = 0 V \text{ to } 3 V, I_D = 10 mA$		350		ns
Turn-off time *	$t_{off}$	$V_{DD} = 3 V, V_{GS} = 3 V \text{ to } 0 V, I_D = 10 mA$		350		ns

■ Electrical Characteristics (continued)  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$ 

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \* :  $t_{\text{on}}$ ,  $t_{\text{off}}$  measurement circuit

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